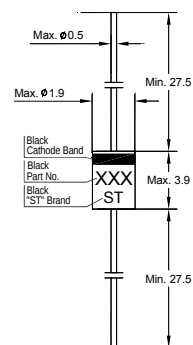


ZPD2V7B...ZPD75B

Silicon Epitaxial Planar Zener Diodes



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	500 ¹⁾	mW
Junction Temperature	T_j	175	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 175	$^{\circ}\text{C}$
¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case.			

Characteristics at $T_a = 25\text{ }^{\circ}\text{C}$

Parameter	Symbol	Max.	Unit
Thermal Resistance Junction to Ambient Air	R_{thA}	0.3 ¹⁾	K/mW
Forward Voltage at $I_F = 100\text{ mA}$	V_F	1	V
¹⁾ Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case.			



CHANGZHOU GUANGDA ELECTRONIC CO. LTD

Dated : 12/06/2009

ZPD2V7B...ZPD75B

Characteristics ($T_a = 25\text{ }^{\circ}\text{C}$ unless otherwise noted)

Type	Zener Voltage Range ¹⁾			Dynamic Resistance			Min. Reverse Voltage V_R (V) at $I_R = 100\text{ nA}$	Admissible Zener Current ²⁾	
	V_{Znom}	V_{ZT}	at I_{ZT}	Z_{ZT}	Z_{ZK}	at I_{ZK}		at $T_a = 45\text{ }^{\circ}\text{C}$	at $T_a = 25\text{ }^{\circ}\text{C}$
	(V)	(V)	(mA)	Max.(Ω)	Max.(Ω)	(mA)		I_Z (mA)	I_Z (mA)
ZPD2V7B	2.7	2.65...2.75	5	83	500	1	-	135	160
ZPD3V0B	3.0	2.94...3.06	5	95	500	1	-	117	140
ZPD3V3B	3.3	3.23...3.37	5	95	500	1	-	109	130
ZPD3V6B	3.6	3.53...3.67	5	95	500	1	-	101	120
ZPD3V9B	3.9	3.82...3.98	5	95	500	1	-	92	110
ZPD4V3B	4.3	4.21...4.39	5	95	500	1	-	85	100
ZPD4V7B	4.7	4.61...4.79	5	78	500	1	-	76	90
ZPD5V1B	5.1	5...5.2	5	60	480	1	0.8	67	80
ZPD5V6B	5.6	5.49...5.71	5	40	400	1	1	59	70
ZPD6V2B	6.2	6.08...6.32	5	10	200	1	2	54	64
ZPD6V8B	6.8	6.66...6.94	5	8	150	1	3	49	58
ZPD7V5B	7.5	7.35...7.65	5	7	50	1	5	44	53
ZPD8V2B	8.2	8.04...8.36	5	7	50	1	6	40	47
ZPD9V1B	9.1	8.92...9.28	5	10	50	1	7	36	43
ZPD10B	10	9.8...10.2	5	15	70	1	7.5	33	40
ZPD11B	11	10.8...11.2	5	20	70	1	8.5	30	36
ZPD12B	12	11.8...12.2	5	20	90	1	9	28	32
ZPD13B	13	12.7...13.3	5	25	110	1	10	25	29
ZPD15B	15	14.7...15.3	5	30	110	1	11	23	27
ZPD16B	16	15.7...16.3	5	40	170	1	12	20	24
ZPD18B	18	17.6...18.4	5	50	170	1	14	18	21
ZPD20B	20	19.6...20.4	5	50	220	1	15	17	20
ZPD22B	22	21.6...22.4	5	55	220	1	17	16	18
ZPD24B	24	23.5...24.5	5	80	220	1	18	13	16
ZPD27B	27	26.5...27.5	5	80	250	1	20	12	14
ZPD30B	30	29.4...30.6	5	80	250	1	22.5	10	13
ZPD33B	33	32.3...33.7	5	80	250	1	25	9	12
ZPD36B	36	35.3...36.7	5	90	250	1	27	9	11
ZPD39B	39	38.2...39.8	5	90	300	1	29	8	10
ZPD43B	43	42.1...43.9	5	100	700	1	32	7	9.2
ZPD47B	47	46.1...47.9	5	100	750	1	35	6	8.5
ZPD51B	51	50...52	5	100	750	1	38	6	7.8
ZPD56B	56	54.9...57.1	2.5	135	1000	0.5	42	5.2	7.1
ZPD62B	62	60.8...63.2	2.5	150	1000	0.5	47	4.8	6.4
ZPD68B	68	66.6...69.4	2.5	200	1000	0.5	51	4.1	5.8
ZPD75B	75	73.5...76.5	2.5	250	1500	0.5	55	3.9	5.3

¹⁾ Tested with pulses $t_p = 20\text{ ms}$.

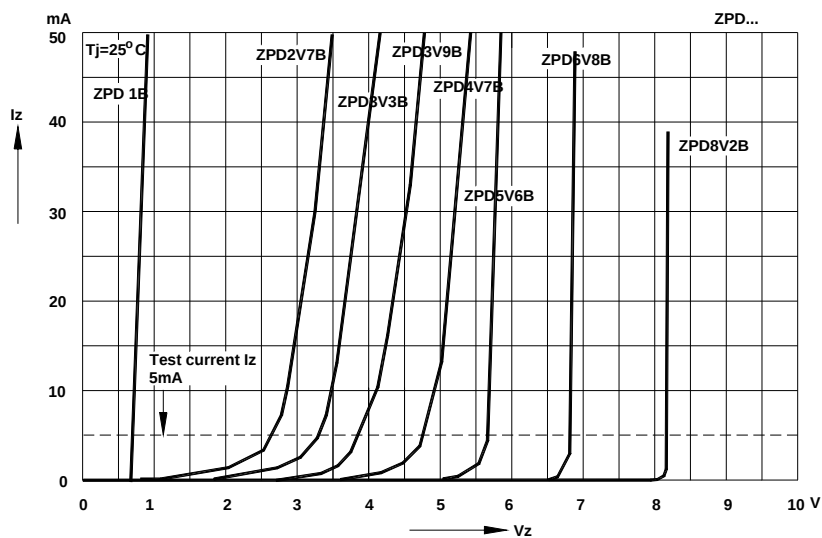
²⁾ Valid provided that leads are kept at ambient temperature at a distance of 8 mm from case.



CHANGZHOU GUANGDA ELECTRONIC CO. LTD

Dated : 12/06/2009

Breakdown characteristics
 $T_j = \text{constant (pulsed)}$



Breakdown characteristics
 $T_j = \text{constant (pulsed)}$

